# L298

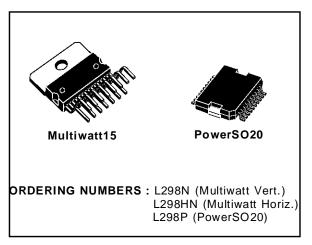


## DUAL FULL-BRIDGE DRIVER

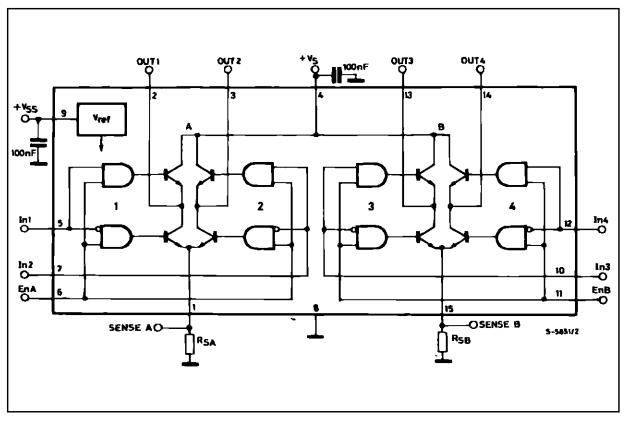
- OPERATING SUPPLY VOLTAGE UP TO 46 V
- TOTAL DC CURRENT UP TO 4 A
- LOW SATURATION VOLTAGE
- OVERTEMPERATURE PROTECTION
- LOGICAL "0" INPUT VOLTAGE UP TO 1.5 V (HIGH NOISE IMMUNITY)

## DESCRIPTION

The L298 is an integrated monolithic circuit in a 15lead Multiwatt and PowerSO20 packages. It is a high voltage, high current dual full-bridge driver designed to accept standard TTL logic levels and drive inductive loads such as relays, solenoids, DC and stepping motors. Two enable inputs are provided to enable or disable the device independently of the input signals. The emitters of the lower transistors of each bridge are connected together and the corresponding external terminal can be used for the con-



nection of an external sensing resistor. An additional supply input is provided so that the logic works at a lower voltage.



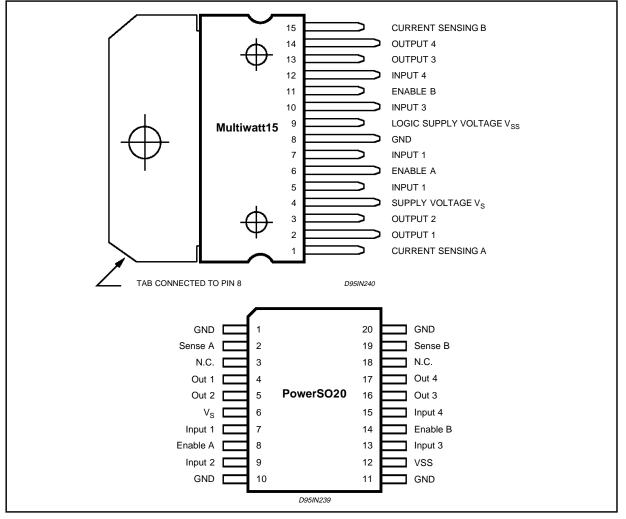
## BLOCK DIAGRAM

## L298

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Power Supply	50	V
Vss	Logic Supply Voltage	7	V
$V_{I}, V_{en}$	Input and Enable Voltage	–0.3 to 7	V
IO	Peak Output Current (each Channel) – Non Repetitive (t = 100µs) –Repetitive (80% on –20% off; t <sub>on</sub> = 10ms) –DC Operation	3 2.5 2	A A A
Vsens	Sensing Voltage	-1 to 2.3	V
Ptot	Total Power Dissipation ( $T_{case} = 75^{\circ}C$ )	25	W
T <sub>stg</sub> , T <sub>j</sub>	Storage and Junction Temperature	-40 to 150	°C

## **PIN CONNECTIONS** (top view)



## THERMAL DATA

Symbol	Parameter		PowerSO20	Multiwatt15	Unit
R <sub>th j-case</sub>	Thermal Resistance Junction-case	Max.	_	3	°C/W
R <sub>th j-amb</sub>	Thermal Resistance Junction-ambient	Max.	13 (*)	35	°C/W

(\*) Mounted on aluminum substrate



MW.15	PowerSO	Name	Function
1;15	2;19	Sense A; Sense B	Between this pin and ground is connected the sense resistor to control the current of the load.
2;3	4;5	Out 1; Out 2	Outputs of the Bridge A; the current that flows through the load connected between these two pins is monitored at pin 1.
4	6	Vs	Supply Voltage for the Power Output Stages. A non-inductive 100nF capacitor must be connected between this pin and ground.
5;7	7;9	Input 1; Input 2	TTL Compatible Inputs of the Bridge A.
6;11	8;14	Enable A; Enable B	TTL Compatible Enable Input: the L state disables the bridge A (enable A) and/or the bridge B (enable B).
8	1,10,11,20	GND	Ground.
9	12	VSS	Supply Voltage for the Logic Blocks. A100nF capacitor must be connected between this pin and ground.
10; 12	13;15	Input 3; Input 4	TTL Compatible Inputs of the Bridge B.
13; 14	16;17	Out 3; Out 4	Outputs of the Bridge B. The current that flows through the load connected between these two pins is monitored at pin 15.
_	3;18	N.C.	Not Connected

## PIN FUNCTIONS (refer to the block diagram)

## **ELECTRICAL CHARACTERISTICS** ( $V_S = 42V$ ; $V_{SS} = 5V$ , $T_j = 25^{\circ}C$ ; unless otherwise specified)

Symbol	Parameter	Test Conditi	ons	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 4)	Operative Condition		V <sub>IH</sub> +2.5		46	V
$V_{SS}$	Logic Supply Voltage (pin 9)			4.5	5	7	V
Is	Quiescent Supply Current (pin 4)	$V_{en} = H; I_L = 0$	$V_i = L$ $V_i = H$		13 50	22 70	mA mA
		V <sub>en</sub> = L	$V_i = X$			4	mA
I <sub>SS</sub>	Quiescent Current from $V_{SS}$ (pin 9)	$V_{en} = H; I_L = 0$	$V_i = L$ $V_i = H$		24 7	36 12	mA mA
		$V_{en} = L$	$V_i = X$			6	mA
V <sub>iL</sub>	Input Low Voltage (pins 5, 7, 10, 12)			-0.3		1.5	V
V <sub>iH</sub>	Input High Voltage (pins 5, 7, 10, 12)			2.3		VSS	V
l <sub>iL</sub>	Low Voltage Input Current (pins 5, 7, 10, 12)	$V_i = L$				-10	μΑ
liн	High Voltage Input Current (pins 5, 7, 10, 12)	$Vi = H \le V_{SS} - 0.6V$			30	100	μΑ
$V_{en} = L$	Enable Low Voltage (pins 6, 11)			-0.3		1.5	V
$V_{en} = H$	Enable High Voltage (pins 6, 11)			2.3		V <sub>SS</sub>	V
$I_{en} = L$	Low Voltage Enable Current (pins 6, 11)	V <sub>en</sub> = L				-10	μΑ
I <sub>en</sub> = H	High Voltage Enable Current (pins 6, 11)	$V_{en} = H \le V_{SS} - 0.6V$			30	100	μΑ
V <sub>CEsat (H)</sub>	Source Saturation Voltage	I <sub>L</sub> = 1A I <sub>L</sub> = 2A			1.35 2	1.7 2.7	V V
V <sub>CEsat (L)</sub>	Sink Saturation Voltage	$I_L = 1A$ (5) $I_L = 2A$ (5)			1.2 1.7	1.6 2.3	V V
V <sub>CEsat</sub>	Total Drop	$I_L = 1A$ (5) $I_L = 2A$ (5)				3.2 4.9	V V
V <sub>sens</sub>	Sensing Voltage (pins 1, 15)			-1 (1)		2	V



Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
T1 (Vi)	Source Current Turn-off Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (2); (4)		1.5		μs
T <sub>2</sub> (V <sub>i</sub> )	Source Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (2); (4)		0.2		μs
T3 (Vi)	Source Current Turn-on Delay	0.5 Vi to 0.1 I∟ (2); (4)		2		μs
T <sub>4</sub> (V <sub>i</sub> )	Source Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (2); (4)		0.7		μs
T <sub>5</sub> (V <sub>i</sub> )	Sink Current Turn-off Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (3); (4)		0.7		μs
T <sub>6</sub> (V <sub>i</sub> )	Sink Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (3); (4)		0.25		μs
T <sub>7</sub> (V <sub>i</sub> )	Sink Current Turn-on Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (3); (4)		1.6		μs
T <sub>8</sub> (V <sub>i</sub> )	Sink Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (3); (4)		0.2		μs
fc (Vi)	Commutation Frequency	$I_L = 2A$		25	40	KHz
T <sub>1</sub> (V <sub>en</sub> )	Source Current Turn-off Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (2); (4)		3		μs
T <sub>2</sub> (V <sub>en</sub> )	Source Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (2); (4)		1		μs
T <sub>3</sub> (V <sub>en</sub> )	Source Current Turn-on Delay	0.5 V <sub>en</sub> to 0.1 I <sub>L</sub> (2); (4)		0.3		μs
T <sub>4</sub> (V <sub>en</sub> )	Source Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (2); (4)		0.4		μs
T <sub>5</sub> (V <sub>en</sub> )	Sink Current Turn-off Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (3); (4)		2.2		μs
T <sub>6</sub> (V <sub>en</sub> )	Sink Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (3); (4)		0.35		μs
T <sub>7</sub> (V <sub>en</sub> )	Sink Current Turn-on Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (3); (4)		0.25		μs
T <sub>8</sub> (V <sub>en</sub> )	Sink Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (3); (4)		0.1		μs
fc (V <sub>en</sub> )	Commutation Frequency	$I_L = 2A$		1		KHz

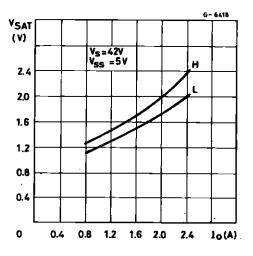
#### ELECTRICAL CHARACTERISTICS (continued)

1) 1)Sensing voltage can be –1 V for t  $\leq$  50  $\mu sec;$  in steady state  $V_{sens}$  min  $\geq$  – 0.5 V.

2) See fig. 2.

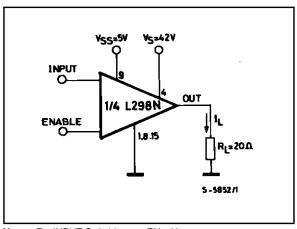
3) See fig. 4.

4) The load must be a pure resistor.
5) PIN 1 and PIN 15 connected to GND.



#### Figure 1 : Typical Saturation Voltage vs. Output Current.

Figure 2 : Switching Times Test Circuits.



Note : For INPUT Switching, set EN = H For ENABLE Switching, set IN = H



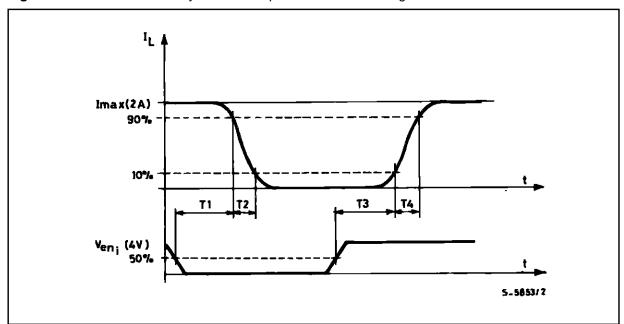
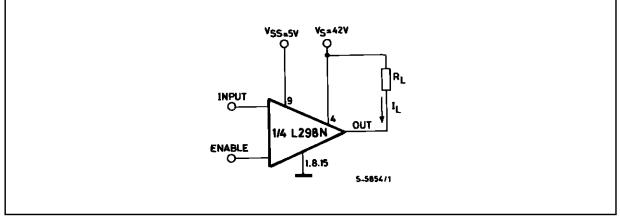


Figure 3 : Source Current Delay Times vs. Input or Enable Switching.

Figure 4 : Switching Times Test Circuits.



Note : For INPUT Switching, set EN = H For ENABLE Switching, set IN = L



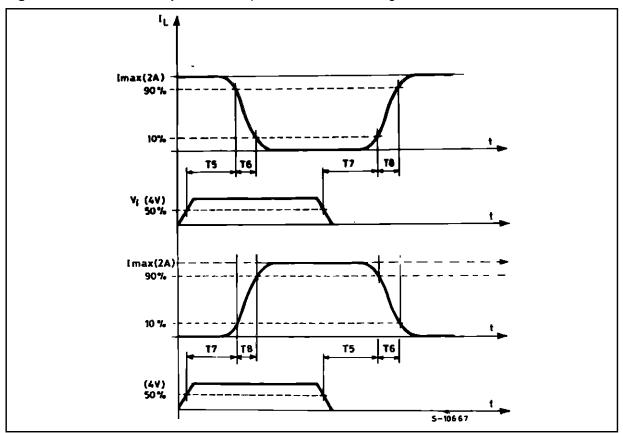
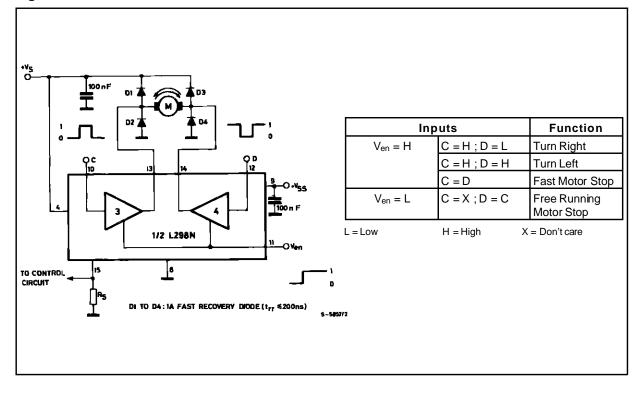
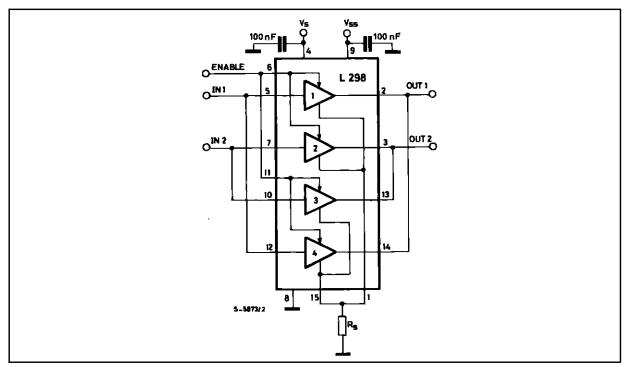


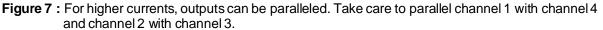
Figure 5 : Sink Current Delay Times vs. Input 0 V Enable Switching.

Figure 6 : Bidirectional DC Motor Control.









## **APPLICATION INFORMATION (Refer to the block diagram)**

## 1.1. POWER OUTPUT STAGE

The L298 integrates two power output stages (A; B). The power output stage is a bridge configuration and its outputs can drive an inductive load in common or differenzial mode, depending on the state of the inputs. The current that flows through the load comes out from the bridge at the sense output : an external resistor ( $R_{SA}$ ;  $R_{SB}$ .) allows to detect the intensity of this current.

## 1.2. INPUT STAGE

Each bridge is driven by means of four gates the input of which are In1; In2; EnA and In3; In4; EnB. The In inputs set the bridge state when The En input is high; a low state of the En input inhibits the bridge. All the inputs are TTL compatible.

## 2. SUGGESTIONS

A non inductive capacitor, usually of 100 nF, must be foreseen between both Vs and Vss, to ground, as near as possible to GND pin. When the large capacitor of the power supply is too far from the IC, a second smaller one must be foreseen near the L298.

The sense resistor, not of a wire wound type, must be grounded near the negative pole of Vs that must be near the GND pin of the I.C. Each input must be connected to the source of the driving signals by means of a very short path.

Turn-On and Turn-Off : Before to Turn-ON the Supply Voltage and before to Turn it OFF, the Enable input must be driven to the Low state.

## 3. APPLICATIONS

Fig 6 shows a bidirectional DC motor control Schematic Diagram for which only one bridge is needed. The external bridge of diodes D1 to D4 is made by four fast recovery elements (trr  $\leq$  200 nsec) that must be chosen of a VF as low as possible at the worst case of the load current.

The sense output voltage can be used to control the current amplitude by chopping the inputs, or to provide overcurrent protection by switching low the enable input.

The brake function (Fast motor stop) requires that the Absolute Maximum Rating of 2 Amps must never be overcome.

When the repetitive peak current needed from the load is higher than 2 Amps, a paralleled configuration can be chosen (See Fig.7).

An external bridge of diodes are required when inductive loads are driven and when the inputs of the IC are chopped; Shottky diodes would be preferred.



This solution can drive until 3 Amps In DC operation and until 3.5 Amps of a repetitive peak current.

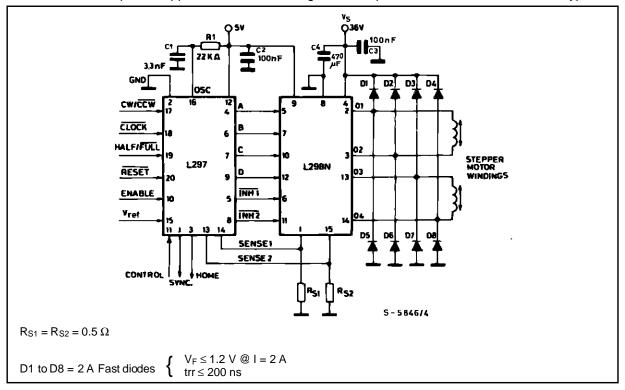
On Fig 8 it is shown the driving of a two phase bipolar stepper motor ; the needed signals to drive the inputs of the L298 are generated, in this example, from the IC L297.

Fig 10 shows a second two phase bipolar stepper motor control circuit where the current is controlled by the I.C. L6506.

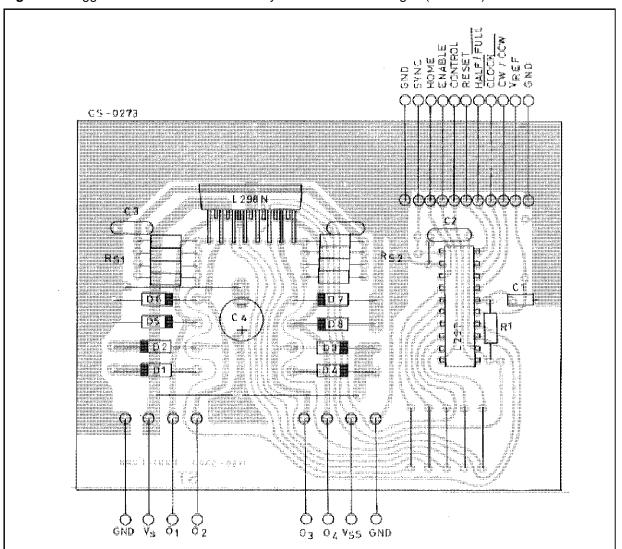
Fig 9 shows an example of P.C.B. designed for the application of Fig 8.

Figure 8 : Two Phase Bipolar Stepper Motor Circuit.

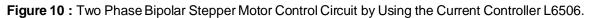
This circuit drives bipolar stepper motors with winding currents up to 2 A. The diodes are fast 2 A types.

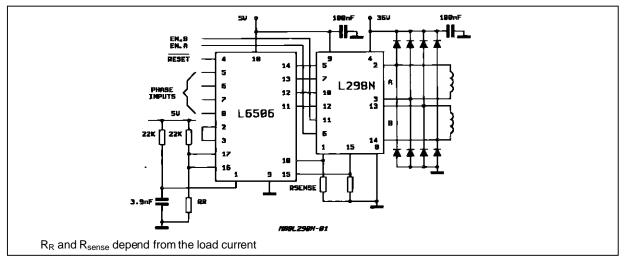








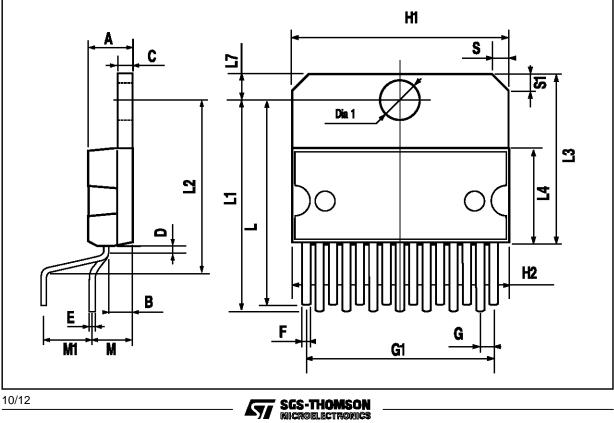






## L298

DIM.	mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			5			0.197	
В			2.65			0.104	
С			1.6			0.063	
D		1			0.039		
E	0.49		0.55	0.019		0.022	
F	0.66		0.75	0.026		0.030	
G	1.14	1.27	1.4	0.045	0.050	0.055	
G1	17.57	17.78	17.91	0.692	0.700	0.705	
H1	19.6			0.772			
H2			20.2			0.795	
L	22.1		22.6	0.870		0.890	
L1	22		22.5	0.866		0.886	
L2	17.65		18.1	0.695		0.713	
L3	17.25	17.5	17.75	0.679	0.689	0.699	
L4	10.3	10.7	10.9	0.406	0.421	0.429	
L7	2.65		2.9	0.104		0.114	
М	4.2	4.3	4.6	0.165	0.169	0.181	
M1	4.5	5.08	5.3	0.177	0.200	0.209	
S	1.9		2.6	0.075		0.102	
S1	1.9		2.6	0.075		0.102	
Dia1	3.65		3.85	0.144		0.152	

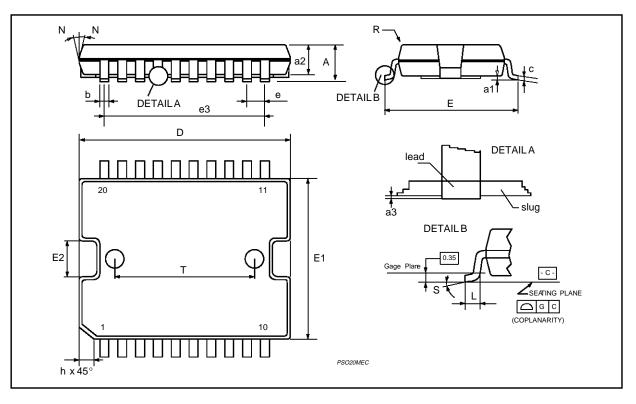


DIM.	mm			inch			
DIW.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			3.60			0.1417	
a1	0.10		0.30	0.0039		0.0118	
a2			3.30			0.1299	
a3	0		0.10	0		0.0039	
b	0.40		0.53	0.0157		0.0209	
С	0.23		0.32	0.009		0.0126	
D (1)	15.80		16.00	0.6220		0.6299	
E	13.90		14.50	0.5472		0.570	
е		1.27			0.050		
e3		11.43			0.450		
E1 (1)	10.90		11.10	0.4291		0.437	
E2			2.90			0.1141	
G	0		0.10	0		0.0039	
h			1.10				
L	0.80		1.10	0.0314		0.0433	
N			10°	(max.)			
S	8° (max.)						
Т		10.0			0.3937		

## PowerSO20 PACKAGE MECHANICAL DATA

(1) "D and E1" do not include mold flash or protrusions

- Mold flash or protrusions shall not exceed 0.15mm (0.006")



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